

1. Description

This P-Channel MOSFET is a rugged gate version of advanced PowerTrench process. It has been optimized for power management applications requiring a wide range of gate drive voltage ratings (4.5V – 25V).

2. Features

- High power and current handling capability
- High performance trench technology for extremely low $R_{DS(ON)}$

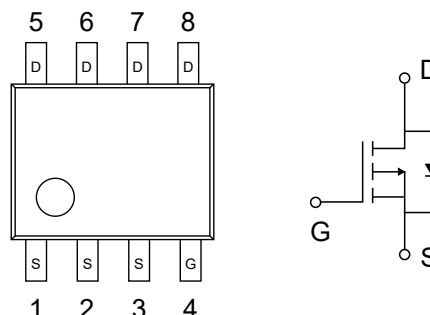
2.1 Features

- $V_{DS(V)} = -30V$
- $I_D = -5.3A$
- $R_{DS(ON)} < 50m\Omega (V_{GS} = -10V)$
- $R_{DS(ON)} < 80m\Omega (V_{GS} = -4.5V)$

3. Pinning information

Pin	Symbol	Description
4	G	GATE
1,2,3	S	SOURCE
5,6,7,8	D	DRAIN

SOP-8



4. Absolute Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V_{GSS}	± 25	V
Drain Current – Continuous	I_D	-5.3	A
– Pulsed (Note 1a)		-50	
Power Dissipation for Single Operation	P_D	2.5	W
		1.2	
		1	
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ C$



5. Thermal Characteristics

Parameter	Symbol	Rating	Units
Thermal Resistance, Junction-to-Ambient (Note 1a)	$R_{\theta JA}$	50	°C/W
Thermal Resistance, Junction-to-Ambient (Note 1c)	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction-to-Case (Note 1)	$R_{\theta JC}$	25	°C/W



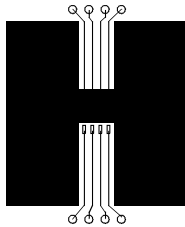
6. Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-30			V
Breakdown Voltage Temperature Coefficient	$\frac{\Delta BV_{DSS}}{\Delta T_J}$	$I_D=-250\mu\text{A}$ Referenced to 25°C		-23		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24\text{V}$, $V_{GS}=0\text{V}$			-1	μA
Gate-Body Leakage, Forward	I_{GSSF}	$V_{GS}=25\text{V}$, $V_{DS}=0\text{V}$			100	nA
Gate-Body Leakage, Reverse	I_{GSSR}	$V_{GS}=-25\text{V}$, $V_{DS}=0\text{V}$			-100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-1	-1.7	-3	V
Gate Threshold Voltage Temperature Coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	$I_D=-250\mu\text{A}$ Referenced to 25°C		4.5		mV/ $^\circ\text{C}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10\text{V}$, $I_D=-5.3\text{A}$ $V_{GS}=-4.5\text{V}$, $I_D=-4\text{A}$		42 65	50 80	m Ω m Ω
On-State Drain Current	$I_{D(on)}$	$V_{GS}=-10\text{V}$, $V_{DS}=-5\text{V}$	-25			A
Forward Transconductance	g_{FS}	$V_{DS}=-5\text{V}$, $I_D=-5.3\text{A}$		10		S
Input Capacitance	C_{iss}	$V_{DS}=-15\text{V}$		528		pF
Output Capacitance	C_{oss}	$V_{GS}=0\text{V}$		132		pF
Reverse Transfer Capacitance	C_{rss}	$f=1\text{MHz}$		70		pF
Turn-On DelayTime	$t_{D(on)}$	$V_{DD}=-15\text{V}$, $I_D=-1\text{A}$ $V_{GS}=-10\text{V}$, $R_{GEN}=6\Omega$		7	14	ns
Turn-On Rise Time	t_r			13	24	ns
Turn-Off DelayTime	$t_{D(off)}$			14	25	ns
Turn-Off Fall Time	t_f			9	17	ns
Total Gate Charge	Q_g	$V_{DS}=-15\text{V}$, $I_D=-4\text{A}$ $V_{GS}=-10\text{V}$		10	14	nC
Gate-Source Charge	Q_{gs}			2.2		nC
Gate-Drain Charge	Q_{gd}			2		nC
Maximum Continuous Drain-Source Diode Forward Current	I_S				-2.1	A
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{V}$, $I_S=-2.1\text{A}$ (Note 2)		-0.8	-1.2	V

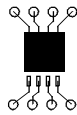


Notes:

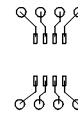
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50° C/W when
mounted on a 1 in²
pad of 2 oz. copper.



b) 105° C/W when
mounted on a 0.4 in²
pad of 2 oz. copper.



c) 125° C/W when
mounted on a minimum
pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%



7.1 TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

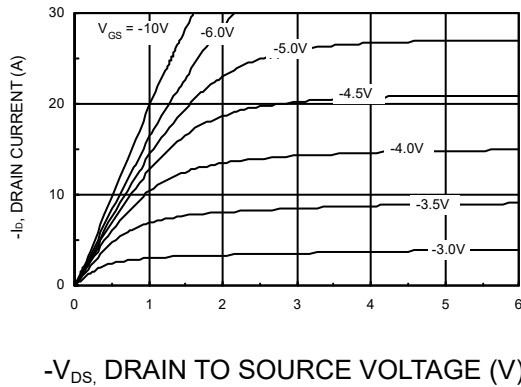


Fig 1: On-Region Characteristics.

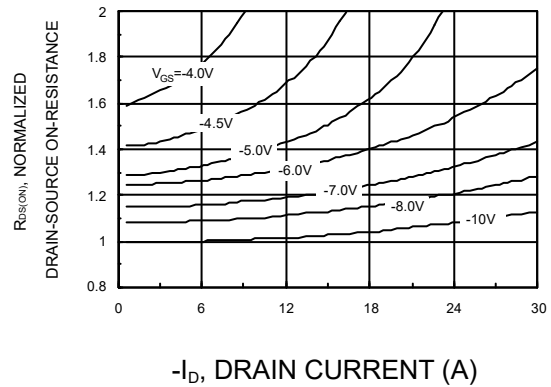


Figure 2: On-Resistance Variation with Drain Current and Gate Voltage.

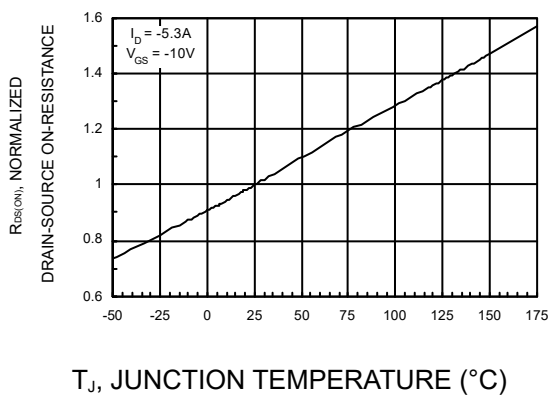


Figure 3: On-Resistance Variation with Temperature.

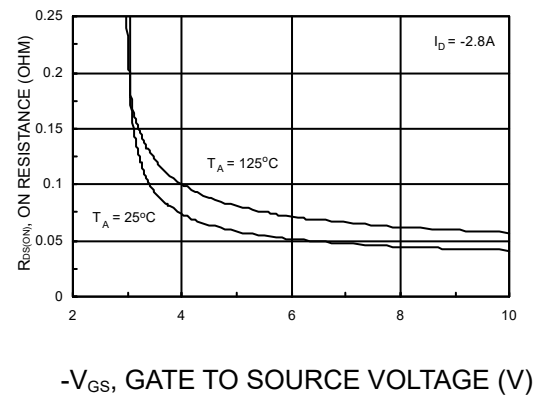


Figure 4: On-Resistance Variation with Gate-to-Source Voltage.

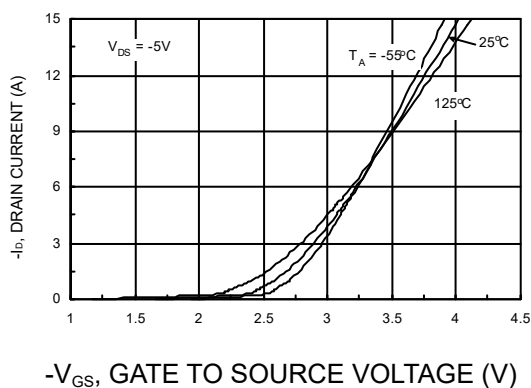


Figure 5: Transfer Characteristics.

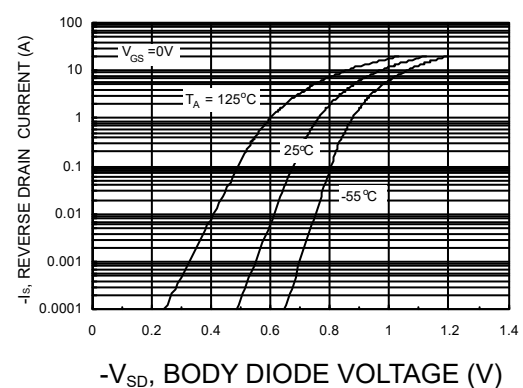


Figure 6: . Body Diode Forward Voltage Variation with Source Current and Temperature.



7.2 TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

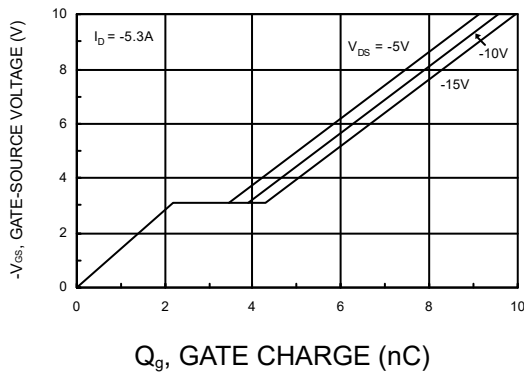


Figure 7: Gate-Charge Characteristics

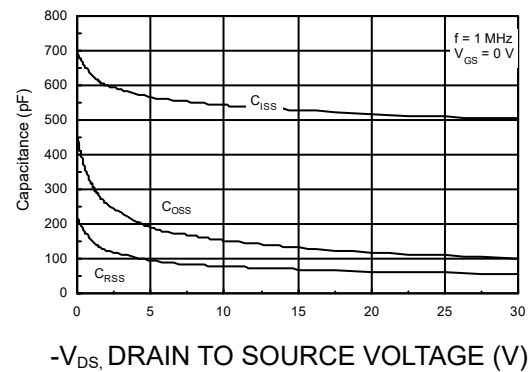


Figure 8: Capacitance Characteristics

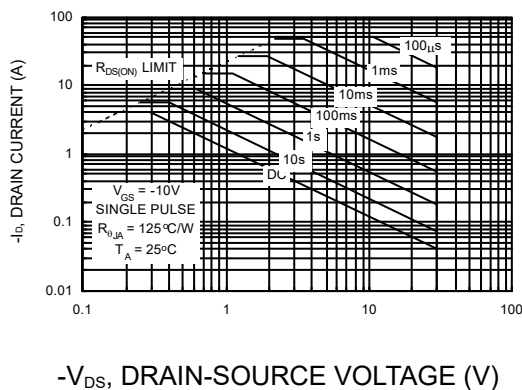


Figure 9: Maximum Safe Operating Area.

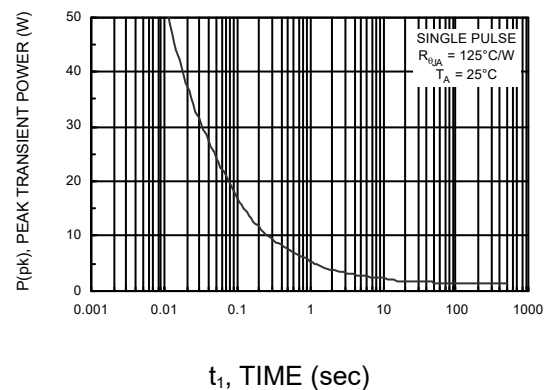


Figure 10: Single Pulse Maximum Power Dissipation.

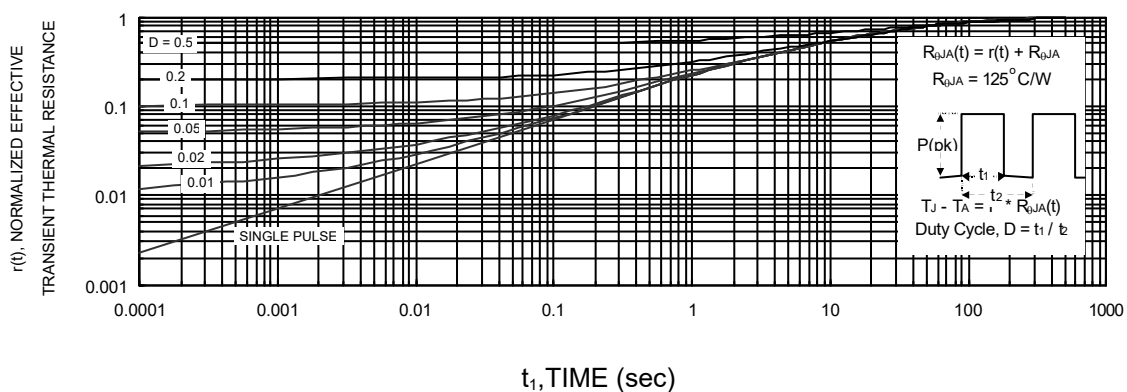
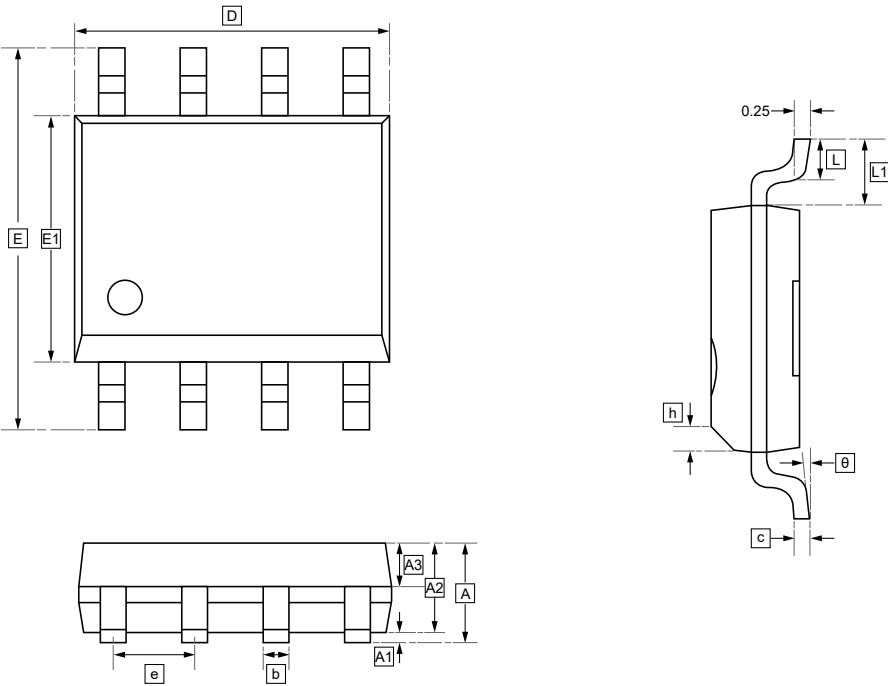


Figure 11: Transient Thermal Response Curve.



8.SOP-8 Package Outline Dimensions



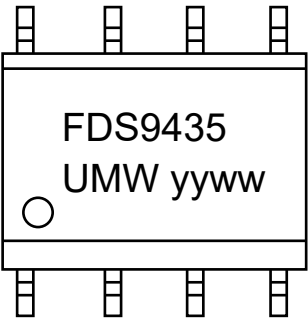
DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A2	A3	b	c	D	E	E1	e	h	L
Min	-	0.05	1.30	0.60	0.39	0.20	4.80	5.80	3.80	1.24	0.30	0.50
Max	1.75	0.20	1.50	0.70	0.47	0.24	5.00	6.20	4.00	1.30	0.50	0.80

Symbol	L1	θ
Min	1.00	0°
Max	1.10	8°



9.Ordering information



yy: Year Code
ww: Week Code

Order Code	Package	Base QTY	Delivery Mode
UMW FDS9435A	SOP-8	3000	Tape and reel



10.Disclaimer

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